TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

# MT3S07S

#### VHF~UHF Band Low Noise Amplifier Applications

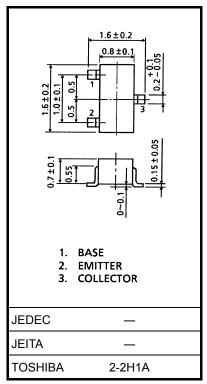
Unit: mm

- Low noise figure: NF = 1.5dB (VCE = 3 V, IC = 5 mA, f = 2 GHz)
- High gain:  $|S_{21e}|^2 = 9.5 dB$  ( $V_{CE} = 3 V$ ,  $I_{C} = 15 mA$ , f = 2 GHz)

#### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V <sub>CBO</sub>	10	V
Collector-emitter voltage	V <sub>CEO</sub>	5	V
Emitter-base voltage	V <sub>EBO</sub>	1.5	V
Collector current	IC	25	mA
Base current	Ι <sub>Β</sub>	10	mA
Collector power dissipation	PC	100	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Weight: 0.0024 g (typ.)

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### Marking



#### **Microwave Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Transition frequency	f <sub>T</sub>	$V_{CE} = 3 \text{ V}, I_{C} = 10 \text{ mA}$	10	12	_	GHz
Insertion gain	S <sub>21e</sub>   <sup>2</sup> (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	7.5	_	dB
	S <sub>21e</sub>   <sup>2</sup> (2)	$V_{CE} = 3 \text{ V}, I_{C} = 15 \text{ mA}, f = 2 \text{ GHz}$	6.5	9.5	_	
Noise figure —	NF (1)	$V_{CE} = 1 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$		1.6	3	dB
	NF (2)	$V_{CE} = 3 \text{ V}, I_{C} = 5 \text{ mA}, f = 2 \text{ GHz}$	_	1.5	3	uБ

### Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = 5 V, I <sub>E</sub> = 0	_	_	0.1	μА
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 1 V, I <sub>C</sub> = 0	_	_	1	μΑ
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = 1 V, I <sub>C</sub> = 5 mA	70	_	140	
Reverse transfer capacitance	C <sub>re</sub>	$V_{CB} = 1 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$ (Note)		0.4	0.85	pF

Note:  $C_{\text{re}}$  is measured by 3 terminal method with capacitance bridge.

## Caution

This device is sensitive to electrostatic discharge. Please handle with caution.

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#### **RESTRICTIONS ON PRODUCT USE**

20070701-EN GENERAL

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